SN65LVCP22
SLLS553B-NOVEMBER 2002-REVISED JUNE 2003

## 2x2 LVDS CROSSPOINT SWITCH

## FEATURES

- High Speed ( $>1000 \mathrm{Mbps}$ ) Upgrade for DS90CP22 2x2 LVDS Crosspoint Switch
- LVPECL Crosspoint Switch Available in SN65LVCP23
- Low-Jitter Fully Differential Data Path
- 50 ps (Typ), of Peak-to-Peak Jitter With PRBS $=2^{23}-1$ Pattern
- Less Than 200 mW (Typ), 300 mW (Max) Total Power Dissipation
- Output (Channel-to-Channel) Skew Is 10 ps (Typ), 50 ps (Max)
- Configurable as 2:1 Mux, 1:2 Demux, Repeater or 1:2 Signal Splitter
- Inputs Accept LVDS, LVPECL, and CML Signals
- Fast Switch Time of 1.7 ns (Typ)
- Fast Propagation Delay of 0.65 ns (Typ)
- 16 Lead SOIC and TSSOP Packages
- Inter-Operates With TIA/EIA-644-A LVDS Standard
- Operating Temperature: $-40^{\circ} \mathrm{C}$ to $85^{\circ} \mathrm{C}$


## APPLICATIONS

- Base Stations
- Add/Drop Muxes
- Protection Switching for Serial Backplanes
- Network Switches/Routers
- Optical Networking Line Cards/Switches
- Clock Distribution


## DESCRIPTION

The SN65LVCP22 is a $2 \times 2$ crosspoint switch providing greater than 1000 Mbps operation for each path. The dual channels incorporate wide common-mode ( 0 V to 4 V ) receivers, allowing for the receipt of LVDS, LVPECL, and CML signals. The dual outputs are LVDS drivers to provide low-power, low-EMI, high-speed operation. The SN65LVCP22 provides a single device supporting 2:2 buffering (repeating), 1:2 splitting, 2:1 multiplexing, $2 \times 2$ switching, and LVPECL/CML to LVDS level translation on each channel. The flexible operation of the SN65LVCP22 provides a single device to support the redundant serial bus transmission needs (working and protection switching cards) of fault-tolerant switch systems found in optical networking, wireless infrastructure, and data commu- nications systems. TI offers additional gigibit repeater/ translator and crosspoint products in the SN65LVDS100 and SN65LVDS122.
The SN65LVCP22 uses a fully differential data path to ensure low-noise generation, fast switching times, low pulse width distortion, and low jitter. Output channel-to- channel skew is less than 10 ps (typ) and 50 ps (max) to ensure accurate alignment of outputs in all applications. Both SOIC and TSSOP package options are available to allow easy upgrade for existing solutions, and board area savings where space is critical.


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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ORDERING INFORMATION

| PACKAGE DESIGNATOR | PART NUMBER $^{(1)}$ | SYMBOLIZATION |
| :---: | :---: | :---: |
| SOIC | SN65LVCP22D | LVCP22 |
| TSSOP | SN65LVCP22PW | LVCP22 |

(1) Add the suffix $R$ for taped and reeled carrier

## PACKAGE DISSIPATION RATINGS

| PACKAGE | CIRCUIT BOARD MODEL | $\begin{gathered} \mathrm{T}_{\mathrm{A}} \leq 25^{\circ} \mathrm{C} \\ \text { POWER RATING } \end{gathered}$ | DERATING FACTOR ${ }^{(1)}$ <br> ABOVE $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ | $\begin{gathered} \mathrm{T}_{\mathrm{A}}=85^{\circ} \mathrm{C} \\ \text { POWER RATING } \end{gathered}$ |
| :---: | :---: | :---: | :---: | :---: |
| SOIC (D) | High-K ${ }^{(2)}$ | 1361 mW | $13.9 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ | 544 mW |
| TSSOP (PW) | High-K ${ }^{(2)}$ | 1074 mW | $10.7 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ | 430 mW |

(1) This is the inverse of the junction-to-ambient thermal resistance when board-mounted and with no air flow.
(2) In accordance with the High-K thermal metric definitions of EIA/JESD51-7.

## THERMAL CHARACTERISTICS

| PARAMETER |  | TEST CONDITIONS | VALUE | UNITS |  |
| :--- | :--- | :--- | :--- | :---: | :---: |
| $\theta_{\mathrm{JB}}$ | Junction-to-board thermal resistance | D |  | 11.2 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
|  |  | PW |  | 18.4 |  |
| $\theta_{\mathrm{JC}}$ | Junction-to-case thermal resistance | D |  | 23.7 |  |
|  |  | PW |  | 16.0 |  |
| $\mathrm{P}_{\mathrm{D}} \mathrm{C} / \mathrm{W}$ |  |  |  |  |  |
|  | Device power dissipation | Typical | $\mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=25^{\circ} \mathrm{C}, 1 \mathrm{Gbps}$ | 198 |  |
|  |  | Maximum | $\mathrm{V}_{\mathrm{CC}}=3.6 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=85^{\circ} \mathrm{C}, 1 \mathrm{Gbps}$ | c |  |

FUNCTION TABLE

| SELO | SEL1 | OUT0 | OUT1 | FUNCTION |
| :---: | :---: | :---: | :---: | :---: |
| 0 | 0 | IN0 | IN0 | $1: 2$ Splitter |
| 0 | 1 | IN0 | IN1 | Repeater |
| 1 | 0 | IN1 | IN0 | Switch |
| 1 | 1 | IN1 | IN1 | $1: 2$ Splitter |

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## EQUIVALENT INPUT AND OUTPUT SCHEMATIC DIAGRAMS



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ABSOLUTE MAXIMUM RATINGS
over operating free-air temperature range unless otherwise noted ${ }^{(1)}$

|  | UNITS |  |
| :--- | :---: | :---: |
| Supply voltage ${ }^{(2)}$ range, $\mathrm{V}_{\mathrm{CC}}$ | -0.5 V to 4 V |  |
| CMOS/TTL input voltage (ENO, EN1, SEL0, SEL1) | -0.5 V to 4 V |  |
| LVDS receiver input voltage (IN+, IN-) | -0.7 V to 4.3 V |  |
| LVDS driver output voltage (OUT+, OUT-) | -0.5 V to 4 V |  |
| LVDS output short circuit current | Continuous |  |
| Storage temperature range | $-65^{\circ} \mathrm{C}$ to $125^{\circ} \mathrm{C}$ |  |
| Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds | $235^{\circ} \mathrm{C}$ |  |
| Continuous power dissipation | See Dissipation Rating Table |  |
| Electrostatic discharge | Human body model ${ }^{(3)}$ | All pins |
|  | Charged-device mode ${ }^{(4)}$ | All pins |

(1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltage values, except differential I/O bus voltages, are with respect to network ground terminals.
(3) Tested in accordance with JEDEC Standard 22, Test Method A114-A.
(4) Tested in accordance with JEDEC Standard 22, Test Method C101.

RECOMMENDED OPERATING CONDITIONS

|  | MIN | NOM | MAX |
| :--- | ---: | ---: | ---: |
| UNIT |  |  |  |
| Supply voltage, $\mathrm{V}_{\mathrm{CC}}$ | 3 | 3.3 | 3.6 |
| Receiver input voltage | 0 | V |  |
| Junction temperature |  | V |  |
| Operating free-air temperature, $\mathrm{T}_{\mathrm{A}}{ }^{(1)}$ | -40 | 125 | ${ }^{\circ} \mathrm{C}$ |
| Magnitude of differential input voltage $\left\|\mathrm{V}_{\text {ID }}\right\|$ | 0.1 | 85 | ${ }^{\circ} \mathrm{C}$ |

(1) Maximum free-air temperature operation is allowed as long as the device maximum junction temperature is not exceeded.

## INPUT ELECTRICAL CHARACTERISTICS

over recommended operatingconditions unless otherwise noted

|  | PARAMETER | TEST CONDITIONS | MIN | TYP ${ }^{(1)}$ | MAX | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| CMOS/TTL DC SPECIFICATIONS (EN0, EN1, SELO, SEL1) |  |  |  |  |  |  |
| $\mathrm{V}_{\mathrm{IH}}$ | High-level input voltage |  | 2 |  | $\mathrm{V}_{\mathrm{CC}}$ | V |
| $\mathrm{V}_{\mathrm{IL}}$ | Low-level input voltage |  | GND |  | 0.8 | V |
| $\mathrm{I}_{\mathrm{H}}$ | High-level input current | $\mathrm{V}_{\mathrm{IN}}=3.6 \mathrm{~V}$ or $2.0 \mathrm{~V}, \mathrm{~V}_{\mathrm{CC}}=3.6 \mathrm{~V}$ |  | $\pm 3$ | $\pm 20$ | $\mu \mathrm{A}$ |
|  | Low-level input current | $\mathrm{V}_{\text {IN }}=0.0 \mathrm{~V}$ or $0.8 \mathrm{~V}, \mathrm{~V}_{\mathrm{CC}}=3.6 \mathrm{~V}$ |  | $\pm 1$ | $\pm 10$ | $\mu \mathrm{A}$ |
| $\mathrm{V}_{\mathrm{CL}}$ | Input clamp voltage | $\mathrm{I}_{\mathrm{CL}}=-18 \mathrm{~mA}$ |  | -0.8 | -1.5 | V |
| LVDS OUTPUT SPECIFICATIONS (OUT0, OUT1) |  |  |  |  |  |  |
| \|VOD| | Differential output voltage | $\mathrm{R}_{\mathrm{L}}=75 \Omega$, See Figure ${ }^{\text {d }}$ | 270 | 365 | 475 | mV |
|  |  | $\mathrm{R}_{\mathrm{L}}=75 \Omega, \mathrm{~V}_{\mathrm{CC}}=3.3 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=25^{\circ} \mathrm{C} \text {, See }$ Figure 2 | 285 | 365 | 440 |  |
| $\Delta\left\|\mathrm{V}_{\text {OD }}\right\|$ | Change in differential output voltage magnitude between logic states | $\mathrm{V}_{\mathrm{ID}}= \pm 100 \mathrm{mV}$, See Figure 2 | -25 |  | 25 | mV |
| $\mathrm{V}_{\text {OS }}$ | Steady-state offset voltage | See Figure3 | 1 | 1.2 | 1.45 | V |
| $\Delta \mathrm{V}_{\text {OS }}$ | Change in steady-state offset voltage between logic states | See Figure 3 | -25 |  | 25 | mV |
| $\mathrm{V}_{\text {OC(PP) }}$ | Peak-to-peak common-mode output voltage | See Figure3 |  | 50 | 150 | mV |
| $\mathrm{l}_{\mathrm{Oz}}$ | High-impedance output current | $\mathrm{V}_{\text {OUT }}=\mathrm{GND}$ or $\mathrm{V}_{\mathrm{CC}}$ |  |  | $\pm 10$ | $\mu \mathrm{A}$ |
| IofF | Power-off leakage current | $\mathrm{V}_{\text {CC }}=0 \mathrm{~V}, 1.5 \mathrm{~V} ; \mathrm{V}_{\text {OUT }}=3.6 \mathrm{~V}$ or GND |  |  | $\pm 10$ | $\mu \mathrm{A}$ |
| $\mathrm{l}_{\mathrm{OS}}$ | Output short-circuit current | $\mathrm{V}_{\text {OUT+ }}$ or $\mathrm{V}_{\text {OUT }}=0 \mathrm{~V}$ |  |  | -24 | mA |
| $\mathrm{I}_{\text {OSB }}$ | Both outputs short-circuit current | $\mathrm{V}_{\text {OUT }+}$ and $\mathrm{V}_{\text {OUT }-}=0 \mathrm{~V}$ | -12 |  | 12 | mA |
| $\mathrm{C}_{0}$ | Differential output capacitance | $\mathrm{V}_{1}=0.4 \sin (4 \mathrm{E} 6 \pi \mathrm{t})+0.5 \mathrm{~V}$ |  | 3 |  | pF |
| LVDS RECEIVER DC SPECIFICATIONS (IN0, IN1) |  |  |  |  |  |  |
| $\mathrm{V}_{\text {TH }}$ | Positive-going differential input voltage threshold | See Figure 1 and Table 1 |  |  | 100 | mV |
| $\mathrm{V}_{\text {TL }}$ | Negative-going differential input voltage threshold | See Figure 1] and Table 1 | -100 |  |  | mV |
| $\mathrm{V}_{\text {ID(HYS })}$ | Differential input voltage hysteresis |  |  | 25 |  | mV |
| $\mathrm{V}_{\text {CMR }}$ | Common-mode voltage range | $\mathrm{V}_{\text {ID }}=100 \mathrm{mV}, \mathrm{V}_{\text {CC }}=3.0 \mathrm{~V}$ to 3.6 V | 0.05 |  | 3.95 | V |
| $\mathrm{I}_{\mathrm{N}}$ | Input current | $\mathrm{V}_{\text {IN }}=4 \mathrm{~V}, \mathrm{~V}_{\mathrm{CC}}=3.6 \mathrm{~V}$ or 0.0 |  | $\pm 1$ | $\pm 10$ | $\mu \mathrm{A}$ |
|  |  | $\mathrm{V}_{\mathrm{IN}}=0 \mathrm{~V}, \mathrm{~V}_{\mathrm{CC}}=3.6 \mathrm{~V}$ or 0.0 |  | $\pm 1$ | $\pm 10$ |  |
| $\mathrm{C}_{\text {IN }}$ | Differential input capacitance | $\mathrm{V}_{1}=0.4 \sin (4 \mathrm{E} 6 \pi \mathrm{t})+0.5 \mathrm{~V}$ |  | 3 |  | pF |
| SUPPLY CURRENT |  |  |  |  |  |  |
| $\mathrm{I}_{\text {CCD }}$ | Total supply current | $\begin{aligned} & \mathrm{R}_{\mathrm{L}}=75 \Omega, \mathrm{C}_{\mathrm{L}}=5 \mathrm{pF}, 500 \mathrm{MHz}(1000 \\ & \text { Mbps), EN0=EN1=High } \end{aligned}$ |  | 60 | 87 | mA |
| $\mathrm{I}_{\text {CCz }}$ | 3 -state supply current | EN0 = EN1 = Low |  | 25 | 35 | mA |

(1) All typical values are at $25^{\circ} \mathrm{C}$ and with a $3.3-\mathrm{V}$ supply.

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## SWITCHING CHARACTERISTICS

over recommended operating conditions unless otherwise noted

|  | parameter | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\text {SET }}$ | Input to SEL setup time | See Figure 6 | 1 | 0.5 |  | ns |
| $\mathrm{t}_{\text {HOLD }}$ | Input to SEL hold time | See Figure 6 | 1.1 | 0.5 |  | ns |
| $\mathrm{t}_{\text {SWITCH }}$ | SEL to switched output | See Figure 6 |  | 1.7 | 2.5 | ns |
| $\mathrm{t}_{\mathrm{PHZ}}$ | Disable time，high－level－to－high－impedance | See Figure 5 |  | 2 | 4 | ns |
| $\mathrm{t}_{\mathrm{PLZ}}$ | Disable time，low－level－to－high－impedance | See Figure 5 |  | 2 | 4 | ns |
| $\mathrm{t}_{\text {PZH }}$ | Enable time，high－impedance－to－high－level output | See Figure 5 |  | 2 | 4 | ns |
| $\mathrm{t}_{\text {PZL }}$ | Enable time，high－impedance－to－low－level output | See Figure 5 |  | 2 | 4 | ns |
| $\mathrm{t}_{\text {LHT }}$ | Differential output signal rise time（20\％－80\％）${ }^{(1)}$ | $\mathrm{C}_{\mathrm{L}}=5 \mathrm{pF}$ ，See Figure 4 | 150 | 280 | 450 | ps |
| $\mathrm{t}_{\mathrm{HLT}}$ | Differential output signal fall time（20\％－80\％）${ }^{(1)}$ | $\mathrm{C}_{\mathrm{L}}=5 \mathrm{pF}$ ，See Figure 4 | 150 | 280 | 450 | ps |
| $\mathrm{t}_{\text {JIT }}$ | Added peak－to－peak jitter | $\mathrm{V}_{\mathrm{ID}}=200 \mathrm{mV}, 50 \%$ duty cycle， <br> $\mathrm{V}_{\mathrm{CM}}=1.2 \mathrm{~V}, 500 \mathrm{MHz}, \mathrm{C}_{\mathrm{L}}=5 \mathrm{pF}$ |  | 20 | 40 | ps |
|  |  | $\mathrm{V}_{\text {ID }}=200 \mathrm{mV}$ ， $\mathrm{PRBS}=2^{23}-1$ data pattern， $\mathrm{V}_{\mathrm{CM}}=1.2 \mathrm{~V}$ at $1000 \mathrm{Mbps}, \mathrm{C}_{\mathrm{L}}=5 \mathrm{pF}$ |  | 50 | 105 | ps |
| $\mathrm{t}_{\mathrm{Jrms}}$ | Added random jitter（rms） | $\mathrm{V}_{\text {ID }}=200 \mathrm{mV}, 50 \%$ duty cycle， <br> $\mathrm{V}_{\mathrm{CM}}=1.2 \mathrm{~V}$ at $500 \mathrm{MHz}, \mathrm{C}_{\mathrm{L}}=5 \mathrm{pF}$ |  | 1.1 | 1.8 | $\mathrm{ps}_{\text {RMS }}$ |
| $\mathrm{t}_{\text {PLHD }}$ | Propagation delay time，low－to－high－level output ${ }^{(1)}$ |  | 400 | 650 | 1000 | ps |
| $\mathrm{t}_{\text {PHLD }}$ | Propagation delay time，high－to－low－level output ${ }^{(1)}$ |  | 400 | 650 | 1000 | ps |
| $\mathrm{t}_{\text {skew }}$ | Pulse skew（｜t PLHD $\left.^{-} \mathrm{t}_{\text {PHLD }}\right)^{(2)}$ | $\mathrm{C}_{\mathrm{L}}=5 \mathrm{pF}$ ，See Figure 4 |  | 20 | 100 | ps |
| $\mathrm{t}_{\text {CCS }}$ | Output channel－to－channel skew，splitter mode | $\mathrm{C}_{\mathrm{L}}=5 \mathrm{pF}$ ，See Figure 4 |  | 10 | 50 | ps |
| $\mathrm{f}_{\text {MAX }}$ | Maximum operating frequency ${ }^{(3)}$ |  | 1 |  |  | GHz |

（1）Input： $\mathrm{V}_{I C}=1.2 \mathrm{~V}, \mathrm{~V}_{\mathrm{ID}}=200 \mathrm{mV}, 50 \%$ duty cycle， $1 \mathrm{MHz}, \mathrm{t}_{\mathrm{r}} / \mathrm{t}_{\mathrm{f}}=500 \mathrm{ps}$
（2）$t_{\text {skew }}$ is the magnitude of the time difference between the $t_{\text {PLHD }}$ and $t_{\text {PHLD }}$ of any output of a single device．
（3）Signal generator conditions： $50 \%$ duty cycle， $\mathrm{t}_{\mathrm{r}}$ or $\mathrm{t}_{\mathrm{f}} \leq 100 \mathrm{ps}$（ $10 \%$ to $90 \%$ ），transmitter output criteria：duty cycle $=45 \%$ to $55 \% \mathrm{~V}_{\mathrm{OD}} \geq$ 300 mV ．

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## PARAMETER MEASUREMENT INFORMATION



Figure 1. Voltage and Current Definitions


Figure 2. Differential Output Voltage ( $\mathrm{V}_{\mathrm{OD}}$ ) Test Circuit


NOTE: All input pulses are supplied by a generator having the following characteristics: $\mathrm{t}_{\mathrm{r}}$ or $\mathrm{t}_{\mathrm{f}} \leq 1 \mathrm{~ns}$, pulse-repetition rate (PRR) $=0.5$ Mpps, pulse width $=500 \pm 10 \mathrm{~ns} ; \mathrm{R}_{\mathrm{L}}=100 \Omega ; \mathrm{C}_{\mathrm{L}}$ includes instrumentation and fixture capacitance within $0,06 \mathrm{~mm}$ of the D.U.T.; the measurement of $\mathrm{V}_{\mathrm{OC}(\mathrm{PP})}$ is made on test equipment with a -3 dB bandwidth of at least 300 MHz .

Figure 3. Test Circuit and Definitions for the Driver Common-Mode Output Voltage

## PARAMETER MEASUREMENT INFORMATION (continued)



NOTE: All input pulses are supplied by a generator having the following characteristics: $t_{r}$ or $t_{f} \leq .25$ ns, pulse-repetition rate $(P R R)=0.5 \mathrm{Mpps}$, pulse width $=500 \pm 10 \mathrm{~ns} . \mathrm{C}_{\mathrm{L}}$ includes instrumentation and fixture capacitance within $0,06 \mathrm{~mm}$ of the D.U.T.

Figure 4. Timing Test Circuit and Waveforms


NOTE: All input pulses are supplied by a generator having the following characteristics: $t_{r}$ or $t_{f} \leq 1$ ns, pulse-repetition rate $(P R R)=0.5 \mathrm{Mpps}$, pulse width $=500 \pm 10 \mathrm{~ns} . \mathrm{C}_{\mathrm{L}}$ includes instrumentation and fixture capacitance within $0,06 \mathrm{~mm}$ of the D.U.T.

Figure 5. Enable and Disable Time Circuit and Definitions

Table 1. Receiver Input Voltage Threshold Test

| APPLIED VOLTAGES |  | RESULTING DIFFERENTIAL <br> INPUT VOLTAGE | RESULTING COMMON- <br> MODE INPUT VOLTAGE | OUTPUT ${ }^{(1)}$ |
| :---: | :---: | :---: | :---: | :---: |
| $\mathbf{V}_{\mathbf{I A}}$ | $\mathbf{V}_{\mathbf{I B}}$ | $\mathbf{V}_{\mathbf{I D}}$ | 100 mV |  |
| 1.25 V | 1.15 V | -100 mV | H |  |
| 1.15 V | 1.25 V | 100 mV | 3.95 V | L |
| 4.0 V | 3.9 V | -100 mV | 3.95 V | H |
| 3.9 V | 4.0 V | 100 mV | 0.05 V | H |
| 0.1 V | 0.0 V | -100 mV | 0.05 V | L |
| 0.0 V | 0.1 V | 1000 mV | 1.2 V | H |
| 1.7 V | 0.7 V | -1000 mV | 1.2 V | L |
| 0.7 V | 1.7 V | 1000 mV | 3.5 V | H |
| 4.0 V | 3.0 V | -1000 mV | 3.5 V | L |
| 3.0 V | 4.0 V | 1000 mV | 0.5 V | H |
| 1.0 V | 0.0 V | -1000 mV | 0.5 V | L |
| 0.0 V | 1.0 V |  |  |  |

(1) $\mathrm{H}=$ high level, $\mathrm{L}=$ low level


NOTE: $t_{S E T}$ and $t_{\text {HOLD }}$ times specify that data must be in a stable state before and after mux control switches.
Figure 6. Input to Select for Both Rising and Falling Edge Setup and Hold Times

## TYPICAL CHARACTERISTICS



Figure 7.


Figure 10.

PEAK-TO-PEAK JITTER


Figure 13.


Figure 8.


Figure 11.

PEAK-TO-PEAK JITTER
vs
FREQUENCY


Figure 14.

PROPAGATION DELAY TIME
VS
FREE-AIR TEMPERATURE


Figure 9.
PEAK-TO-PEAK JITTER FREQUENCY


Figure 12.

PEAK-TO-PEAK JITTER
VAT


Figure 15.

## TYPICAL CHARACTERISTICS (continued)



Figure 16.


Figure 17.
PEAK-TO-PEAK JITTER
DATA RATE


Figure 19.

## APPLICATION INFORMATION

TYPICAL APPLICATION CIRCUITS (ECL, PECL, LVDS, etc.)
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Figure 20. Low-Voltage Positive Emitter-Coupled Logic (LVPECL)


Figure 21. Current-Mode Logic (CML)


Figure 22. Single-Ended (LVPECL)


Figure 23. Low-Voltage Differential Signaling (LVDS)

APPLICATION INFORMATION (continued)


Figure 24. $2 \times 2$ Crosspoint


Figure 25. 1:2 Spitter


Figure 26. Dual Repeater


Figure 27. 2:1 MUX
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## PACKAGING INFORMATION

| Orderable Device | Status ${ }^{(1)}$ | Package <br> Type | Package <br> Drawing | Pins Package <br> Qty | Eco Plan ${ }^{(2)}$ | Lead/Ball Finish | MSL Peak Temp ${ }^{(3)}$ |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| SN65LVCP22D | ACTIVE | SOIC | D | 16 | 40 |  <br> no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM |
| SN65LVCP22DG4 | ACTIVE | SOIC | D | 16 | 40 |  <br> no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM |
| SN65LVCP22DR | ACTIVE | SOIC | D | 16 | 2500 |  <br> no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM |
| SN65LVCP22DRG4 | ACTIVE | SOIC | D | 16 | 2500 |  <br> no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM |
| SN65LVCP22PW | ACTIVE | TSSOP | PW | 16 | 90 |  <br> no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM |
| SN65LVCP22PWG4 | ACTIVE | TSSOP | PW | 16 | 90 |  <br> no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM |
| SN65LVCP22PWR | ACTIVE | TSSOP | PW | 16 | 2000 |  <br> no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM |
| SN65LVCP22PWRG4 | ACTIVE | TSSOP | PW | 16 | 2000 |  <br> no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM |

${ }^{(1)}$ The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.
${ }^{(2)}$ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS \& no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The $\mathrm{Pb}-\mathrm{Free} / \mathrm{Green}$ conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed $0.1 \%$ by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb -Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb -Free (RoHS compatible) as defined above.
Green (RoHS \& no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine ( Br ) and Antimony ( Sb ) based flame retardants ( Br or Sb do not exceed $0.1 \%$ by weight in homogeneous material)
${ }^{(3)}$ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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## TAPE AND REEL INFORMATION



| $*$ All dimensions are nominal |  |  |  |  |  |  |  |  |  |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Device | Package <br> Type | Package <br> Drawing | Pins | SPQ | Reel <br> Diameter <br> $(\mathbf{m m})$ | Reel <br> Width <br> $\mathbf{W 1}(\mathbf{m m})$ | A0 <br> $(\mathbf{m m})$ | B0 <br> $(\mathbf{m m})$ | K0 <br> $(\mathbf{m m})$ | P1 <br> $(\mathbf{m m})$ | $\mathbf{W}$ <br> $(\mathbf{m m})$ | Pin1 <br> Quadrant |
| SN65LVCP22DR | SOIC | D | 16 | 2500 | 330.0 | 16.4 | 6.5 | 10.3 | 2.1 | 8.0 | 16.0 | Q1 |
| SN65LVCP22PWR | TSSOP | PW | 16 | 2000 | 330.0 | 12.4 | 6.9 | 5.6 | 1.6 | 8.0 | 12.0 | Q1 |


*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| SN65LVCP22DR | SOIC | D | 16 | 2500 | 346.0 | 346.0 | 33.0 |
| SN65LVCP22PWR | TSSOP | PW | 16 | 2000 | 346.0 | 346.0 | 29.0 |

D (R-PDSO-G16)


NOTES: A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.

C Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed $0.006(0,15)$ each side.
D Body width does not include interlead flash. Interlead flash shall not exceed $0.017(0,43)$ each side.
E. Reference JEDEC MS-012 variation AC.

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NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC-7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.


NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
B. This drawing is subject to change without notice.

Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
D Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
E. Falls within JEDEC MO-153


NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC-7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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